

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	11621	mim	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 09:40
S2	156997	protect\$4 near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:04
S3	26	S1 with S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 09:46
S4	157303	(protect\$4 SRO silicon adj rich adj oxide) near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:20
S5	27	S1 with S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:05
S6	0	S5 not S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:06
S7	1	S5 not S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 11:06
S8	1969	mim near3 capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:48
S9	354	(SRO silicon adj rich adj oxide) near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 18:52
S10	2	S8 with S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:21

S11	2	S8 same S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:21
S12	3	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 14:22
S13	97	S9 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:52
S14	60	S13 and (upper top lower bottom) near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:37
S15	55	S14 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:13
S16	5878	(257/296,303,304,306,307,308). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:14
S17	16	S16 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:16
S18	2	S17 and pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:16
S19	2	S18 and (upper top lower bottom) near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:40
S20	18	S9 with pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:40

S21	1	S20 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:41
S22	7	S9 with silicon near3 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:47
S23	8	S9 same silicon near3 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:05
S24	1	S23 not S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:47
S25	7	S23 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:48
S26	37	S9 and silicon near3 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:48
S27	30	S26 not S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 15:48
S28	21	S27 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:03
S29	586159	19with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:03
S30	20	capacitor with S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:05

S31	1	S30 same silicon near3 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:05
S32	1	S30 and silicon near3 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:05
S33	20	((SRO silicon adj rich adj oxide) near layer) with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 16:48
S34	21	((SRO silicon adj rich adj oxide) near layer) with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 17:01
S35	0	("6468915.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 17:02
S36	2	("6468915").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 17:04
S37	2	("5896314").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 17:04
S38	189	(silicon adj rich adj oxide) near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 18:53
S39	2	((silicon adj rich adj oxide) near layer) with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:01
S40	0	("6586347").URPN.	USPAT	OR	OFF	2005/11/21 18:54
S41	9	("5567635"   "5756396"   "5830804"   "5858875"   "6174797"   "6380066"   "6451687"   "6458722"   "6489230").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/21 18:54

S42	2	S41 and ((silicon adj rich adj oxide) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 18:54
S43	1	10/798959	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 12:55
S44	26	((silicon adj rich adj oxide) near layer) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:02
S45	10	((silicon adj rich adj oxide) near layer) same capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:46
S46	2	((silicon adj rich adj oxide) near protect\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:45
S47	278	((silicon adj rich adj oxide) near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:46
S48	2	((silicon adj rich adj oxide) near3 layer) with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:48
S49	9043	mim	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 16:45
S50	1	((silicon adj rich adj oxide) near3 layer) with S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 16:46
S51	2	((silicon adj rich adj oxide) near3 layer) and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 15:50

S52	15	((silicon near3 rich near3oxide) near3 layer) and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 16:45
S53	1644	mim adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:58
S54	1884	mim adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/14 16:45
S55	8	((silicon near3 rich near3oxide) near3 layer) and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 16:46
S56	2	((silicon adj rich adj oxide) near3 layer) and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 16:46
S57	354730	electrode near "3" (Ta tantalum TaN tantalum adj nitride TaSiN tantalum adj silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:56
S58	3837	electrode near3 (Ta tantalum TaN tantalum adj nitride TaSiN tantalum adj silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:57
S59	1644	mim adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:58
S60	17	S59 with S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 17:58